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(54) Title: PROCESS CHAMBER AND SEMICONDUCTOR PROCESS DEVICE

(54) 发明名称: 工艺腔室及半导体工艺设备

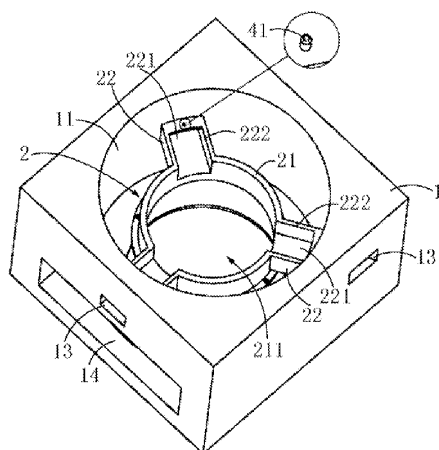


图 1

(57) Abstract: The present invention provides a process chamber and a semiconductor process device. The process chamber is applied to a semiconductor process device, and comprises a chamber body, a base and a chuck assembly; a reaction chamber is formed in the chamber body, the base is located in the reaction chamber, and the chuck assembly is connected to the base for carrying a wafer; the base comprises a base body and a plurality of cantilevers, the plurality of cantilevers are spaced and uniformly arranged in the circumferential direction of the base body, and each cantilever is connected to an inner wall of the chamber body and an outer wall of the base body; and the chamber body, the base body and the cantilevers are integrally formed, and are made of materials having electrical conductivity and thermal conductivity. According to the invention, the radio frequency circuit uniformity and the overall temperature uniformity of the process chamber are greatly improved, thereby greatly increasing the yield of the wafer.

(57) 摘要: 本发明提供了一种工艺腔室及半导体工艺设备。该工艺腔室应用于半导体工艺设备, 包括: 腔室本体、基座及卡盘组件; 腔室本体内形成有反应腔, 基座位于反应腔内, 卡盘组件与基座连接, 用于承载晶圆; 基座包括基座本体和多个悬臂, 多个所述悬臂沿基座本体的周向间隔且均匀设置, 且每个悬臂分别连接腔室本体的内壁和基座本体的外壁; 腔室本体、基座本体和悬臂为一体成型结构, 且由具有导电性和导热性的材质制成。本发明实现了大幅提高工艺腔室的射频回路均匀性及整体温度均匀性, 进而大幅提高晶圆的良率。

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